PCN Number:		20	1603	L60308000 <mark>B</mark>			PC	CN Date	Dec. 5, 20	16
Title:	2ABZQZR <mark>(Addir</mark>	g TP	<mark>S65</mark>	986AB	<mark>ZQZR)</mark>					
Customer	Contact:		<u>PCN</u>	Manager		Dept	t	Qι	uality Services	
Proposed	1 st Ship Date		Mar	5, 2017	Estimated Sam	nple			ate provided at	•
тторозси	1 Ship bate	•	riai	3, 2017	Availability:			sample request.		
Change Type:										
Assen	nbly Site			Assembly Process				Assembly Materials		
Design				Electrical Specification				Mechanical Specification		
Test Site				Packing/Shipping/Labeling				Test Process		
Wafer Bump Site				Wafer Bump Material				Wafer Bump Process		
				Wafer Fab Materials				Wafer F	ab Process	
				Part number change						
	PCN Details									

Description of Change:

The purpose of Revision B of this PCN is to add the TPS65986ABZQZR device to the product affected section of this PCN.

Texas Instruments is pleased to announce the qualification of its DMOS6 fabrication facility as an additional wafer FAB source for TPS65982ABZQZR.

	Current Sites		Additional Sites			
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	
RFAB	LBC8LV	300 mm	DMOS6	LBC8LV	300 mm	

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Changes to product identification resulting from this PCN:

Current

RFAB	RFB	USA	Richardson	
Chip Sites	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City	

New

Chip Site Origin Code Chip Site Country Chip Site City	DMOS6	DM6	USA	Dallas	
Chin Cita Ovinin Coda Chin Cita Country	Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City	

Sample product shipping label (not actual product label)







Product Affected:			
SN1508014ZQZR	SN1508015ZQZR	TPS65982ABZQZR	TPS65986ABZQZR

Qualification Report

TPS65982ABZQZR LBC8LV release in DM6 wafer fab Approve Date 16-Feb-2016

Product Attributes

Attributes	Qual Device: PCD3215B00 BZQZR	Qual Device: PCD3215B00DZ QZR	Qual Device: TPS65982AB ZQZR	QBS Process Reference: CD3215B00 ZQZR	QBS Process Reference: CD3215B00Z QZR	QBS Process Reference: TAS2552YFF	QBS Process Reference: TAS2553YFF
Wafer Fab Supplier	DM0S6	DMOS6	DM0S6	DMOS6	DMOS6	RFAB/DMOS6	RFAB/DMOS6
Wafer Process	LBC8LV	LBC8LV	LBC8LV	LBC8LV	LBC8LV	LBC8LV	LBC8LV

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Test Name / Condition	Duration	Qual Device: PCD3215B00BZQZR	Qual Device: PCD3215B00DZQZR	Qual Device: TPS65982ABZQZR.	QBS Process Reference: CD3215B00ZQZR	QBS Process Reference: CD3215B00ZQZR	QBS Process Reference: TAS2552YFF	QBS Process Reference: TAS2553YFF
ESD - CDM	1000 V	1/3/0	1/3/0	-	2/6/0	1/3/0	-	-
ESD - CDM	1500 V	ı	-	1/3/0	-	-	-	3/9/0
Electrical Characterization	Per Datasheet Parameters	Pass	Pass	Pass	Pass	Pass	-	Pass
Early Life Failure Rate, 125C	48 Hours	-	-	-	2/2000/0	1/1000/ 0	-	-
Early Life Failure Rate, 125C	48 Hours	-	-	-	-	-	-	3/3000/0
Biased HAST, 110C/85%RH	264 Hours	1/77/0	1/77/0	1/77/0	2/154/0	1/77/0	-	-
Biased HAST, 130C/85%RH	96 Hours	ı	-	-	ı	-	3/231/0	-
ESD - HBM	1500 V	1/3/0	-	-	ı	1/3/0	-	3/9/0
ESD - HBM	2000 V	-	-	1/3/0	-	-	-	-
ESD - HBM	2500 V	-	1/3/0	-	2/6/0	-	-	3/9/0
Life Test, 125C	1000 Hours	-	-	-	1/168/0	-	-	-
Life Test, 125C	1000 Hours	1/77/0	1/77/0	1/77/0	2/154/0	1/77/0	-	3/231/0
High Temp. Storage Bake, 150C	1000 Hours	1/77/0	1/77/0	-	2/90/0	1/77/0	-	-
High Temp. Storage Bake, 170C	420 Hours	=	-	1/77/0	-	-	3/228/0	-
Latch-up	(per JESD78)	1/6/0	1/6/0	1/6/0	2/12/0	1/6/0	-	3/18/0
Temperature Cycle, -55/125C	700 Cycles	1/77/0	1/77/0	1/77/0	-	-	3/231/0	-
Unbiased HAST, 110C/85%RH	264 Hours	1/77/0	1/77/0	1/77/0	-	-	-	-
Unbiased HAST, 130C/85%RH	96 Hours	-	-	-	-	-	3/228/0	-

⁻ Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

⁻ The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7 eV: 150 C/1 k Hours, and 170 C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/Green/Pb-free Status: Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

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